

**Silicon PNP Power Transistors**

**2SA1758**

**DESCRIPTION**

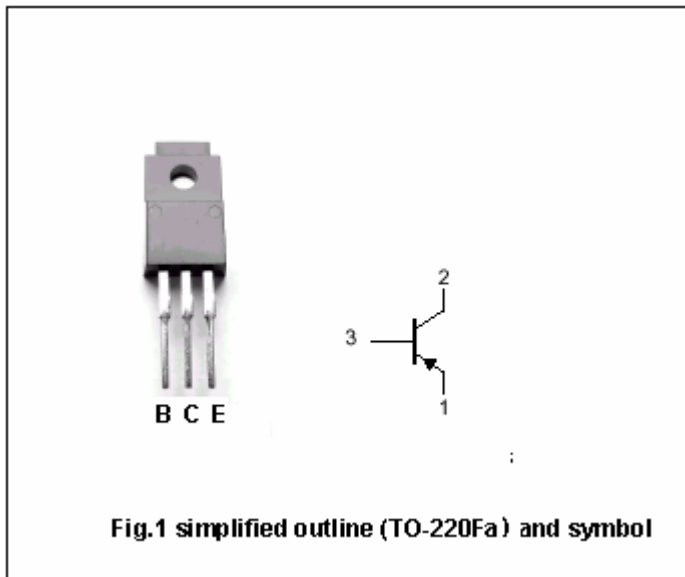
- With TO-220Fa package
- Low collector saturation voltage
- Wide area of safe operation

**APPLICATIONS**

- For power switching applications

**PINNING**

PIN	DESCRIPTION
1	Emitter
2	Collector
3	Base



**Absolute maximum ratings(Ta=25°C)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CB0</sub>	Collector-base voltage	Open emitter	-100	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	-60	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	-5	V
I <sub>C</sub>	Collector current		-12	A
P <sub>C</sub>	Collector power dissipation	T <sub>C</sub> =25°C	30	W
T <sub>j</sub>	Junction temperature		150	°C
T <sub>stg</sub>	Storage temperature		-55~150	°C

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## CHARACTERISTICS

T<sub>j</sub>=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =-1mA, I <sub>B</sub> =0	-60			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =-50μA, I <sub>C</sub> =0	-5			V
V <sub>CEsat-1</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =-6A; I <sub>B</sub> =-0.3A			-0.3	V
V <sub>CEsat-2</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =-8A; I <sub>B</sub> =-0.4A			-0.5	V
V <sub>BEsat-1</sub>	Base-emitter saturation voltage	I <sub>C</sub> =-6A; I <sub>B</sub> =-0.3A			-1.2	V
V <sub>BEsat-2</sub>	Base-emitter saturation voltage	I <sub>C</sub> =-8A; I <sub>B</sub> =-0.4A			-1.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =-100V; I <sub>E</sub> =0			-10	μA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =-5V; I <sub>C</sub> =0			-10	μA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =-2A; V <sub>CE</sub> =-2V	60		320	
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =-1A; V <sub>CE</sub> =-10V		90		MHz

◆ h<sub>FE</sub> Classifications

D	E	F
60-120	100-200	160-320

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PACKAGE OUTLINE

